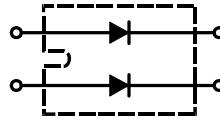


# HiPerDynFRED™ Epitaxial Diode with soft recovery

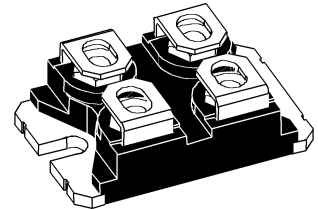
$I_{FAV} = 2 \times 35 \text{ A}$   
 $V_{RRM} = 600 \text{ V}$   
 $t_{rr} = 20 \text{ ns}$

## Preliminary Data

$V_{RSM}$	$V_{RRM}$	Type
V	V	
600	600	DSEP 2x 35-06C



miniBLOC, SOT-227 B



Symbol	Test Conditions	Maximum Ratings	
$I_{FRMS}$		100	A
$I_{FAVM}$	$T_C = 100^\circ\text{C}$ ; rectangular, $d = 0.5$	35	A
$I_{FRM}$	$t_p < 10 \mu\text{s}$ ; rep. rating, pulse width limited by $T_{VJM}$	tbd	A
$I_{FSM}$	$T_{VJ} = 45^\circ\text{C}$ ; $t_p = 10 \text{ ms}$ (50 Hz), sine	300	A
$E_{AS}$	$T_{VJ} = 25^\circ\text{C}$ ; non-repetitive $I_{AS} = 3 \text{ A}$ ; $L = 180 \mu\text{H}$	1.2	mJ
$I_{AR}$	$V_A = 1.5 \cdot V_R$ typ.; $f = 10 \text{ kHz}$ ; repetitive	0.3	A
$T_{VJ}$		-40...+150	$^\circ\text{C}$
$T_{VJM}$		150	$^\circ\text{C}$
$T_{stg}$		-40...+150	$^\circ\text{C}$
$P_{tot}$	$T_C = 25^\circ\text{C}$	210	W
$V_{ISOL}$	50/60 Hz, RMS, $I_{ISOL} \leq 1 \text{ mA}$	2500	V~
$M_d$	mounting torque (M4)	1.1-1.5/9-13	Nm/lb.in.
	terminal connection torque (M4)	1.1-1.5/9-13	Nm/lb.in.
Weight	typical	30	g

## Features

- International standard package miniBLOC
- Isolation voltage 2500 V~
- UL registered E 72873
- 2 independent FRED in 1 package
- Planar passivated chips
- Very short recovery time
- Extremely low switching losses
- Low  $I_{RM}$ -values
- Soft recovery behaviour

## Applications

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode in converters and motor control circuits
- Rectifiers in switch mode power supplies (SMPS)
- Inductive heating
- Uninterruptible power supplies (UPS)
- Ultrasonic cleaners and welders

## Advantages

- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low  $I_{RM}$  reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Symbol	Test Conditions	Characteristic Values	
		typ.	max.
$I_R$ ①	$V_R = V_{RRM}$ ; $T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 150^\circ\text{C}$	0.25	1.0
			mA
$V_F$ ②	$I_F = 35 \text{ A}$ ; $T_{VJ} = 125^\circ\text{C}$ $T_{VJ} = 25^\circ\text{C}$	1.97	2.50
			V
$R_{thJC}$	with heatsink compound	0.1	0.6
$R_{thCH}$			K/W
$t_{rr}$	$I_F = 1 \text{ A}$ ; $-di/dt = 300 \text{ A}/\mu\text{s}$ ; $V_R = 30 \text{ V}$ ; $T_{VJ} = 25^\circ\text{C}$	20	
			ns
$I_{RM}$	$V_R = 100 \text{ V}$ ; $I_F = 50 \text{ A}$ ; $-di_F/dt = 100 \text{ A}/\mu\text{s}$ $T_{VJ} = 100^\circ\text{C}$	4.5	7.0
			A

Pulse test: ① Pulse Width = 5 ms, Duty Cycle < 2.0 %  
 ② Pulse Width = 300  $\mu\text{s}$ , Duty Cycle < 2.0 %

Data according to IEC 60747 and per diode unless otherwise specified

IXYS reserves the right to change limits, test conditions and dimensions.